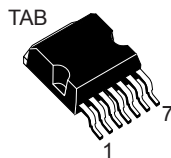
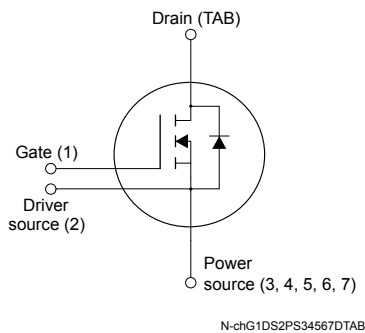


Silicon carbide Power MOSFET 650 V, 45 A, 55 mΩ (typ., T_J = 25 °C) in an H²PAK-7 package


H²PAK-7

Product status link
[SCTH35N65G2V-7](#)
Product summary

Order code	SCTH35N65G2V-7
Marking	SCT35N65
Package	H ² PAK-7
Packing	Tape and reel

Features

Order code	V _{DS}	R _{DS(on)} typ.	I _D
SCTH35N65G2V-7	650 V	55 mΩ	45 A

- Very fast and robust intrinsic body diode
- Low capacitance

Applications

- Switching mode power supply
- EV chargers
- DC-DC converters

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 2nd generation SiC MOSFET technology. The device features remarkably low on-resistance per unit area and very good switching performance. The variation of switching loss is almost independent of junction temperature.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operational values)	-5 to 20	
V _{DS}	Drain-source voltage	650	V
I _D	Drain current (continuous) at T _C = 25 °C	45	A
	Drain current (continuous) at T _C = 100 °C	35	
I _{DM} ⁽¹⁾	Drain current (pulsed)	90	A
P _{TOT}	Total power dissipation at T _C = 25 °C	208	W
T _{stg}	Storage temperature range	-55 to 175	°C
T _J	Operating junction temperature range		°C

1. Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case	0.72	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}$			50	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}, T_J = 175\text{ °C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ to }22\text{ V}$			± 250	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.8	3.2		V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}$		45	67	m Ω
		$V_{GS} = 18\text{ V}, I_D = 20\text{ A}$		55		
		$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 175\text{ °C}$		65		

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 400\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	1370	-	pF
C_{oss}	Output capacitance		-	125	-	pF
C_{rSS}	Reverse transfer capacitance		-	30	-	pF
Q_g	Total gate charge	$V_{DD} = 400\text{ V}, V_{GS} = 0\text{ to }20\text{ V}, I_D = 20\text{ A}$	-	73	-	nC
Q_{gs}	Gate-source charge		-	14	-	nC
Q_{gd}	Gate-drain charge		-	27	-	nC
R_g	Gate input resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	2	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{DD} = 400\text{ V}, I_D = 20\text{ A}$	-	100	-	μJ
E_{off}	Turn-off switching energy	$R_G = 10\text{ }\Omega, V_{GS} = -5\text{ to }20\text{ V}$	-	35	-	μJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}, I_D = 20\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = -5\text{ to }20\text{ V}$	-	16	-	ns
t_f	Fall time		-	14	-	
$t_{d(off)}$	Turn-off delay time		-	35	-	
t_r	Rise time		-	9	-	

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	$I_F = 20\text{ A}$, $V_{GS} = 0\text{ V}$	-	4.5	-	V
t_{rr}	Reverse recovery time	$V_{DD} = 400\text{ V}$, $I_F = 20\text{ A}$, $di/dt = 1000\text{ A}/\mu\text{s}$	-	18	-	ns
Q_{rr}	Reverse recovery charge		-	85	-	nC
I_{RRM}	Reverse recovery current		-	7	-	A

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

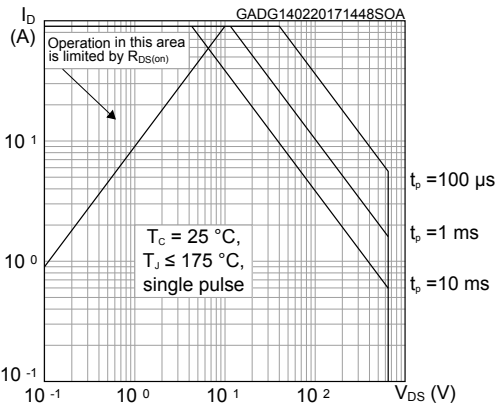


Figure 2. Thermal impedance

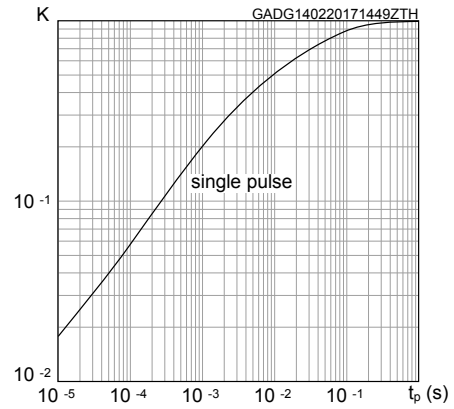


Figure 3. Output characteristics ($T_J = 25 \text{ }^\circ\text{C}$)

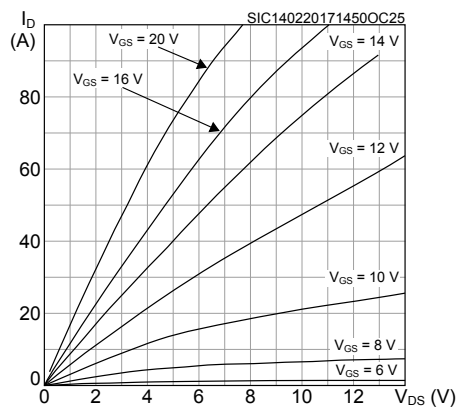


Figure 4. Output characteristics ($T_J = 175 \text{ }^\circ\text{C}$)

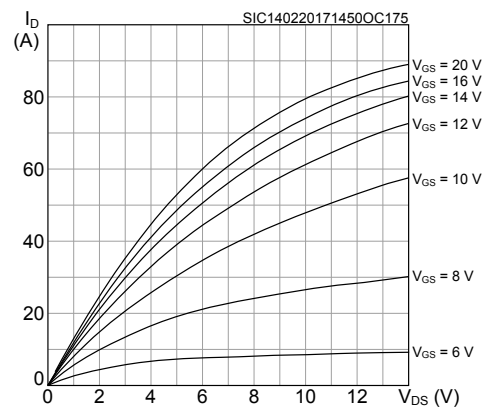


Figure 5. Transfer characteristics

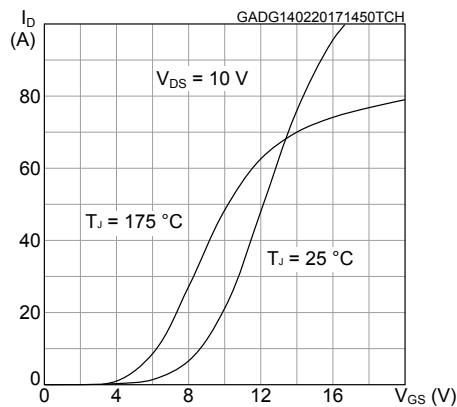


Figure 6. Total power dissipation

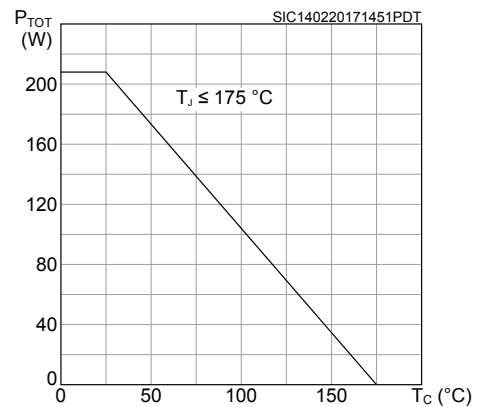


Figure 7. Gate charge vs gate-source voltage

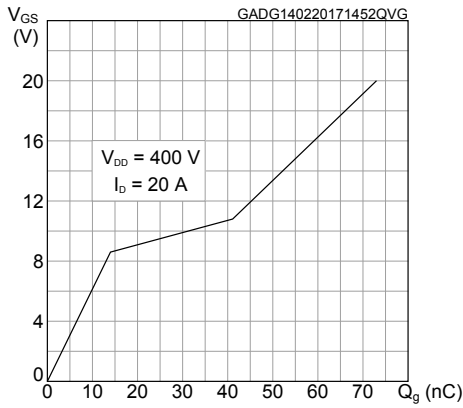


Figure 8. Capacitance variations

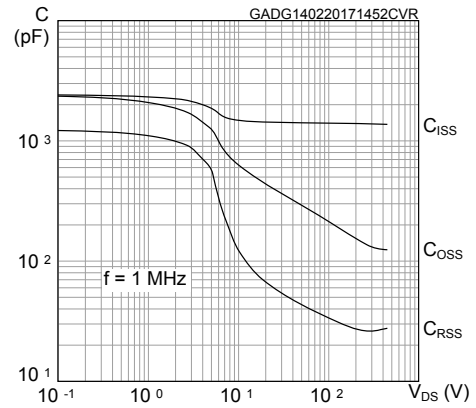


Figure 9. Switching energy vs. drain current

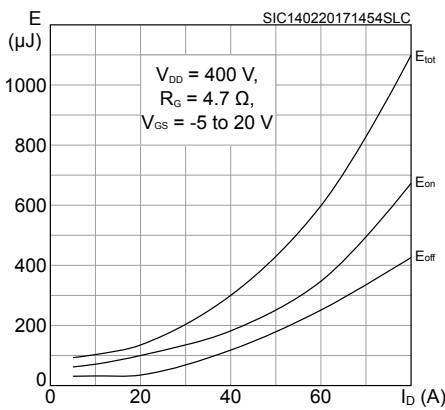


Figure 10. Switching energy vs. junction temperature

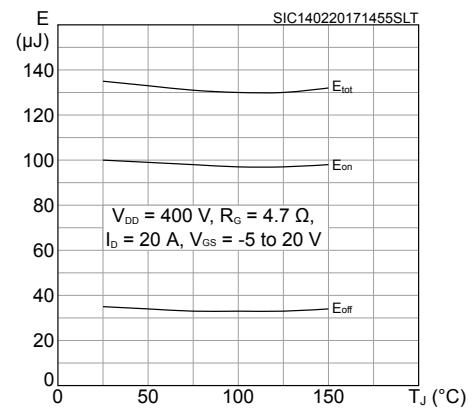


Figure 11. Normalized $V_{(BR)DSS}$ vs. temperature

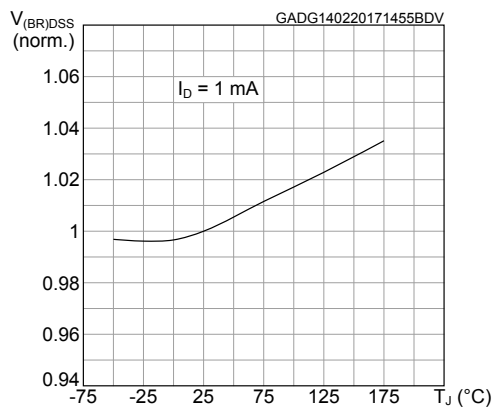


Figure 12. Normalized gate threshold voltage vs. temperature

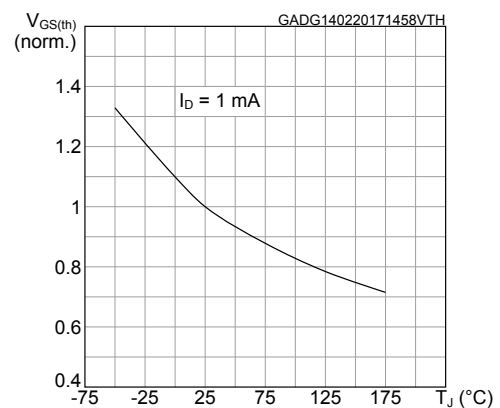


Figure 13. Normalized on-resistance vs. temperature

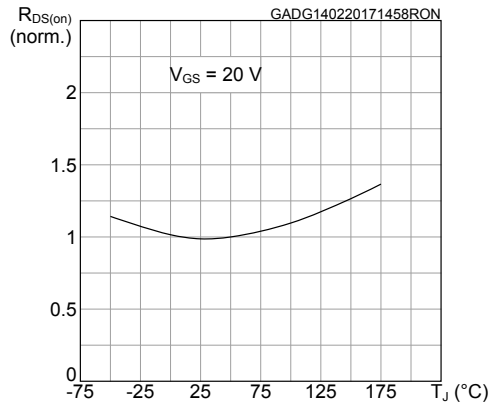


Figure 14. Reverse conduction characteristics ($T_J = 25$ °C)

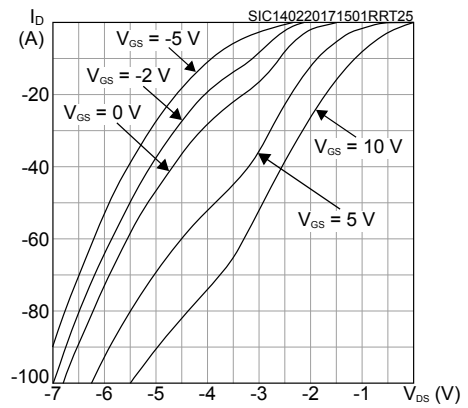
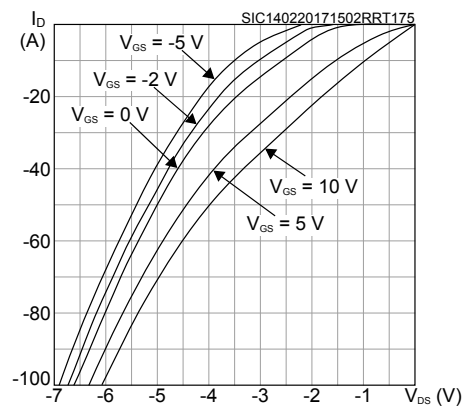
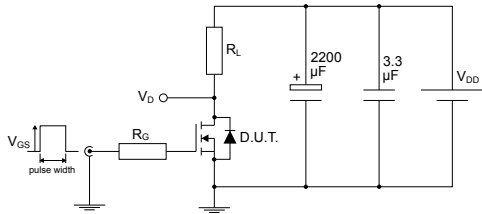


Figure 15. Reverse conduction characteristics ($T_J = 175$ °C)



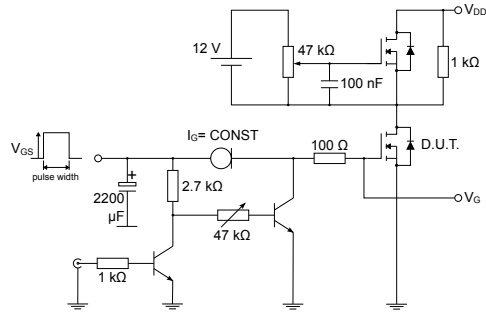
3 Test circuits

Figure 16. Test circuit for resistive load switching times



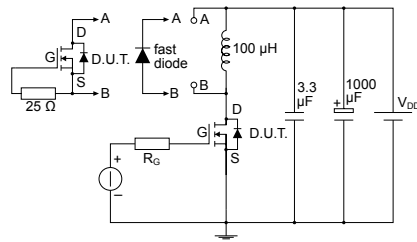
AM01468v1

Figure 17. Test circuit for gate charge behavior



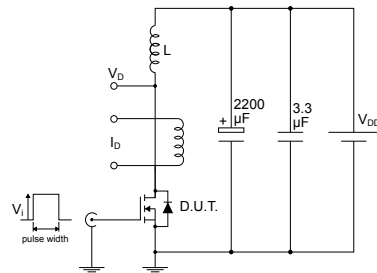
AM01469v1

Figure 18. Test circuit for inductive load switching and diode recovery times



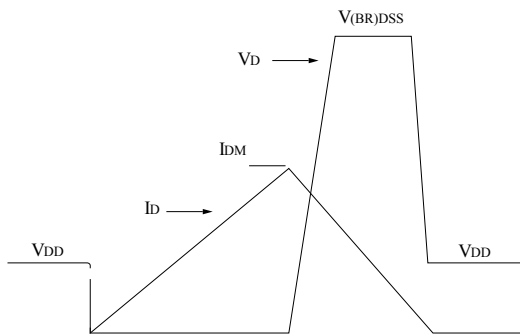
AM01470v1

Figure 19. Unclamped inductive load test circuit



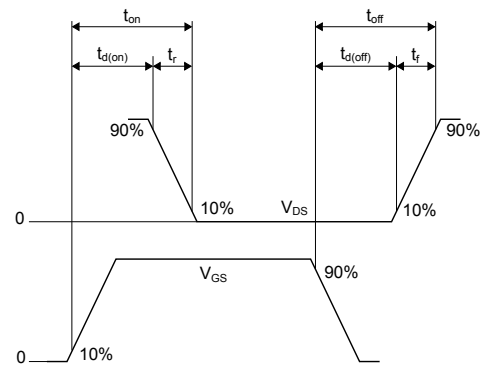
AM01471v1

Figure 20. Unclamped inductive waveform



AM01472v1

Figure 21. Switching time waveform



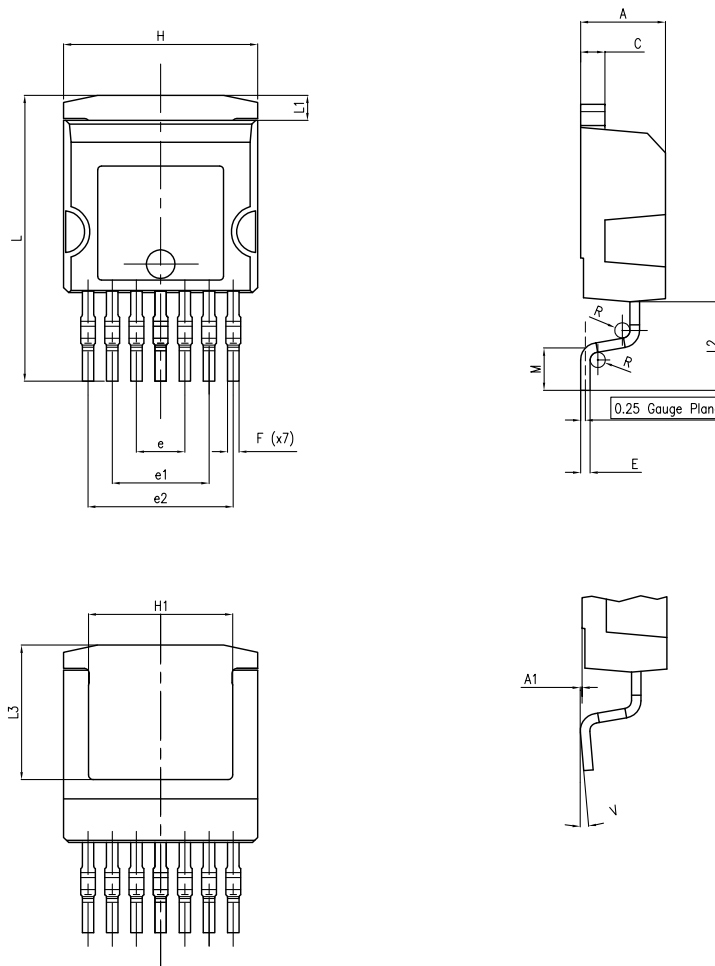
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 H²PAK-7 package information

Figure 22. H²PAK-7 package outline

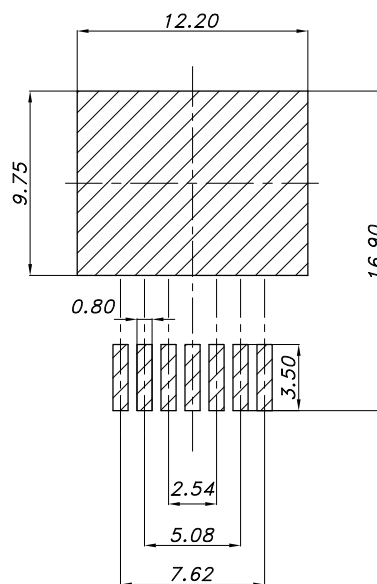


DM00249216_4

Table 8. H²PAK-7 package mechanical data

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	7.60
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

Figure 23. H²PAK-7 recommended footprint

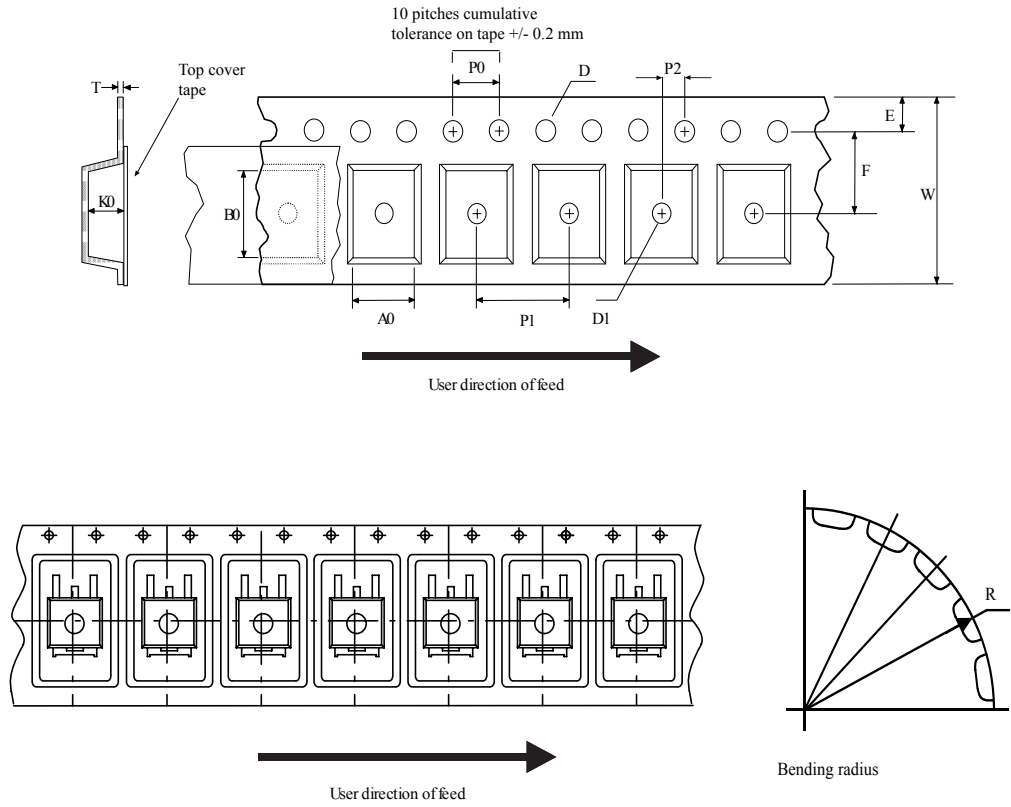


footprint_DM00249216_4

Note: Dimensions are in mm.

4.2 Packing information

Figure 24. Tape outline



AM08852v2

Figure 25. Reel outline

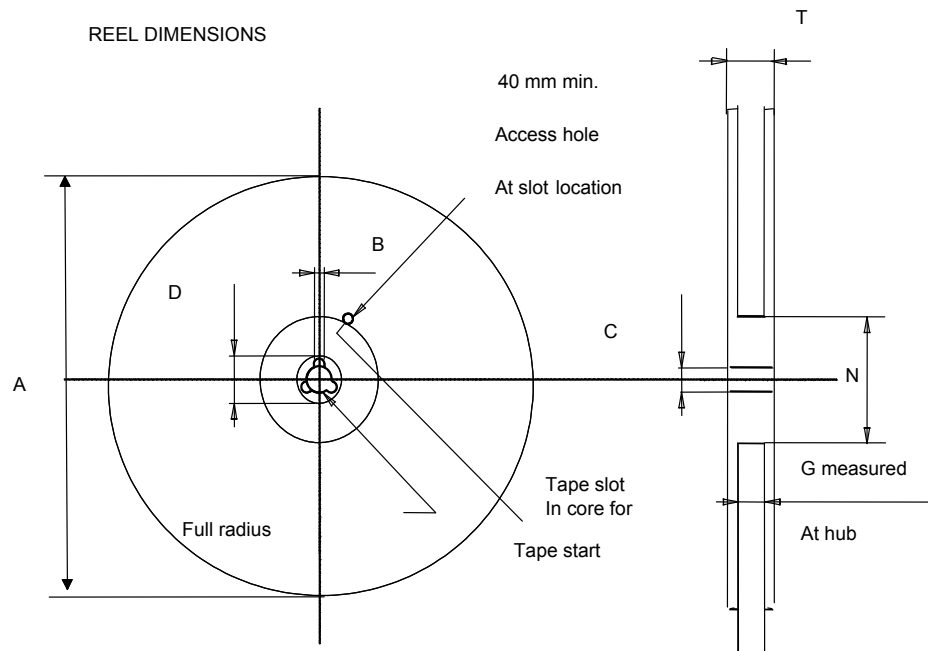


Table 9. Tape and reel mechanical data

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. Document revision history

Date	Version	Changes
27-Feb-2017	1	First release.
12-Dec-2017	2	Modified title. Modified <i>Table 4: "On/off states"</i> . Minor text changes.
03-Oct-2019	3	Updated title, Features and Description in cover page. Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical characteristics (curves)	5
3	Test circuits	8
4	Package information	9
4.1	H ² PAK-7 package information	9
4.2	Packing information	10
	Revision history	13

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